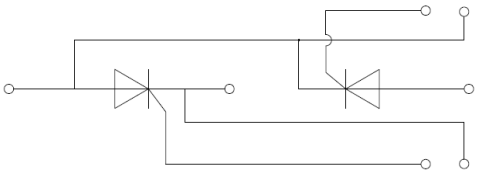
EY cde c Uf V

VRef cVd

Ac Uf TeDf Rc

ARdR VeVc	GR f V	F e
℃		

2 aa TRe d



2 Sd f eV R f CRe Xd

ARdR VeVc	U e d	D S	GR f Vd	F e
	℃			
				℃
				℃

S VTec TR YRdRTeVc de Td

ARdR VeVc	U e d	D S	GR f Vd			F e
				E a	R	
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					

E YVc R YRdRTeVc de Td

dJVc X Wc Re

Vg TV	Rc X	ART RXV	H V XYe	Vc 3	AVc Rœ

E a TR 6 VTec TR E YVc R YRdRTeVc de Td

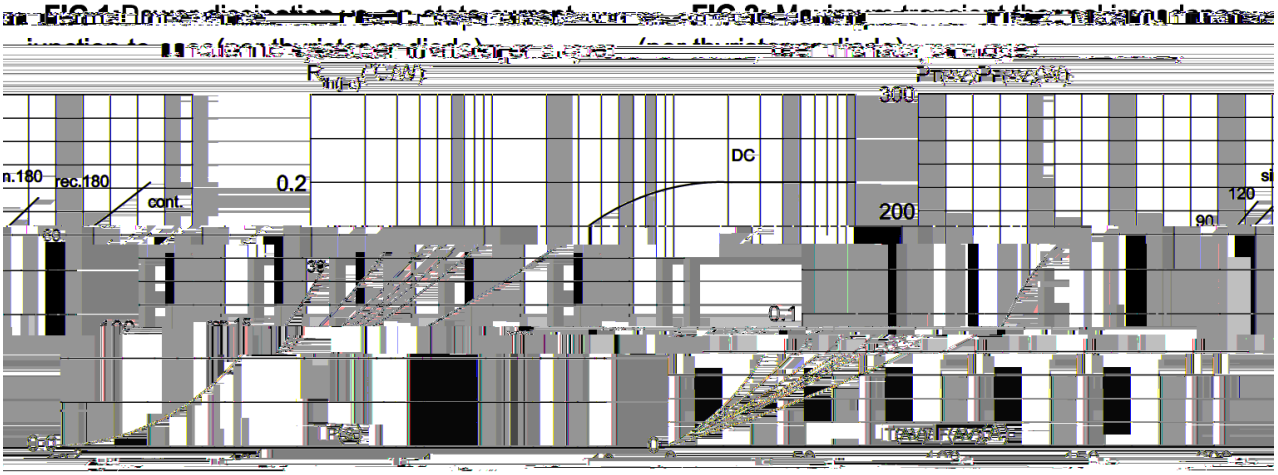


FIG.3: Forward characteristics (per thyristor or diode)

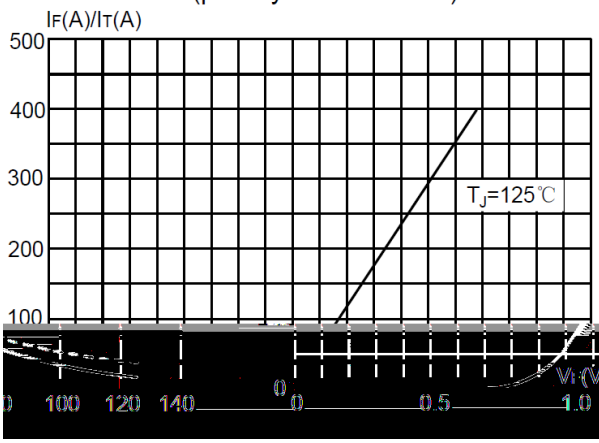


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

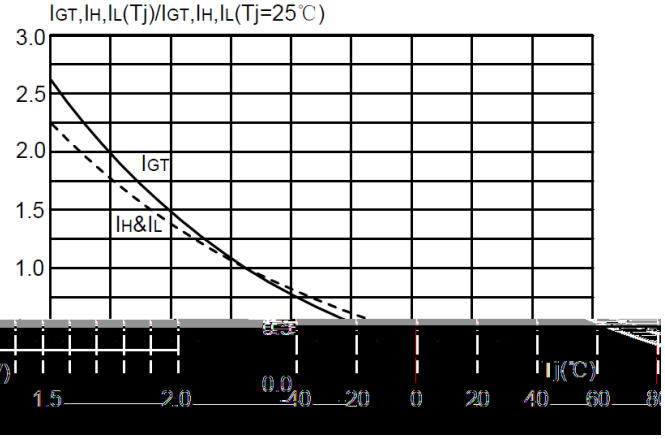


FIG.5 Gate trigger characteristics (per thyristor or diode)

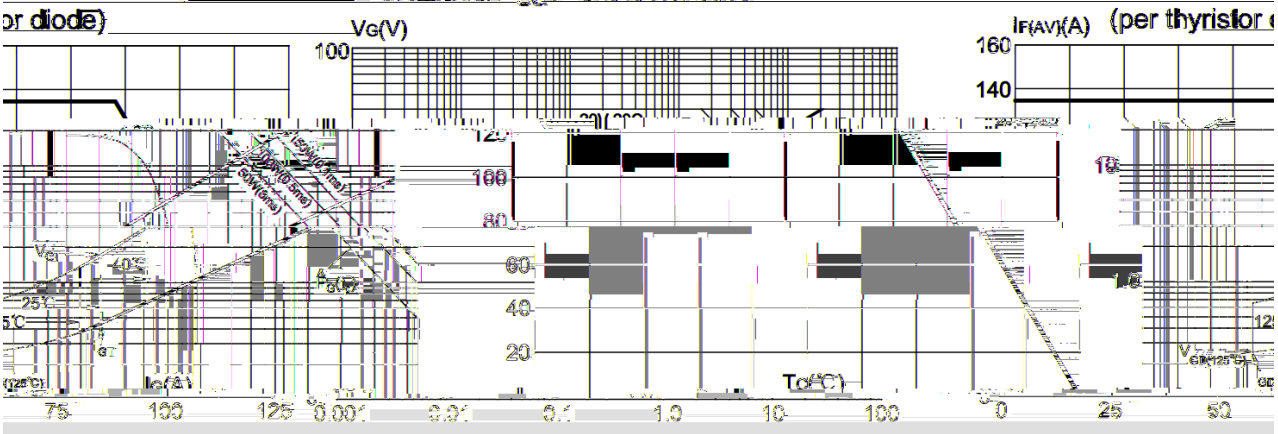


FIG.6: Forward current vs. case temperature (per thyristor

cTf e RXdR

ART RXV f e Vd